| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---------------------|------------------|
| 1 | 3499 | (438/256,299,399,586,597,618,976).CCLS. | USPAT; | 2002/11/10 19:13 |
| | | | US-PGPUB; | |
| İ | | | EPO; JPO; | |
| | | | DERWENT; | |
| _ | | | IBM TDB | |
| 2 | 522 | ((438/256, 299, 399, 586, 597, 618, 976).CCLS.) | USPAT; | 2002/11/10 19:14 |
| | | and metalliz\$5 | US-PGPUB; | 1 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 8 | 54 | | USPAT; | 2002/11/10 19:41 |
| f | | and metalliz\$5) and (arc (antireflect\$4) | US-PGPUB; | |
| | | (anti-reflect\$4)) | EPO; JPO; | ļ |
| | | | DERWENT; | |
| | | ////420/056 000 000 505 505 505 505 | IBM_TDB | |
| 9 | 18 | ((((438/256,299,399,586,597,618,976).CCLS.) | USPAT; | 2002/11/10 19:42 |
| | | and metalliz\$5) and (arc (antireflect\$4) | US-PGPUB; | |
| | | (anti-reflect\$4))) and (plasma adj etch\$3) | EPO; JPO; | |
| | | | DERWENT; | |
| 10 | 18 | //////20/256 200 200 506 507 610 256 | IBM_TDB | |
| 10 | 18 | ((((((438/256,299,399,586,597,618,976).CCLS. | | 2002/11/10 19:42 |
| | | and metalliz\$5) and (arc (antireflect\$4) | US-PGPUB; | |
| | i | <pre>(anti-reflect\$4))) and (plasma adj etch\$3)) and remov\$3</pre> | EPO; JPO; | i |
| | | ecciros)) and temovas | DERWENT; | |
| 12 | 207 | ((438/256,299,399,586,597,618,976).CCLS.) | IBM_TDB USPAT; | 2002/11/10 10:41 |
| | 207 | and (arc (antireflect\$4) (anti-reflect\$4)) | USPAT; US-PGPUB; | 2002/11/10 19:41 |
| 1 | | and (are (ancitetiece,4) (anci-reffect,4)) | EPO; JPO; | |
| 1 | | | DERWENT; | |
| | | | IBM TDB | |
| 14 | 56 | (((438/256,299,399,586,597,618,976).CCLS.) | USPAT; | 2002/11/10 19:42 |
| | 55 | and (arc (antireflect\$4) | US-PGPUB; | 2002/11/10 19.42 |
| | | (anti-reflect\$4))) and (plasma adj etch\$3) | EPO; JPO; | |
| | | (IIIIIIIII IIII (prabilia ad) (cciiyo) | DERWENT; | |
| 1 | | | IBM TDB | |
| 15 | 55 | ((((438/256,299,399,586,597,618,976).CCLS.) | USPAT; | 2002/11/10 19:45 |
| | | and (arc (antireflect\$4) | US-PGPUB; | , |
| | İ | (anti-reflect\$4))) and (plasma adj | EPO; JPO; | <u> </u> |
| į | ĺ | etch\$3)) and remov\$3 | DERWENT; | |
| | | • | IBM TDB | 1 |
| 16 | 2 | (((((438/256,299,399,586,597,618,976).CCLs.) | USPAT; | 2002/11/10 19:46 |
| | ļ | and (arc (antireflect\$4) | US-PGPUB; | |
| İ | ŀ | (anti-reflect\$4))) and (plasma adj | EPO; JPO; | |
| | | etch\$3)) and remov\$3) and (chf3) | DERWENT; | İ |
| | | | IBM TDB | |

| Search | L No. | Hits | Text Search | Data Bases |
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| IS&R | LI | 3043 | ("438/256,299,399,586,597,618,976").C CLS. | USPAT; US-PGPUB; EF 3/1/02 15:45 JPO; DERWENT; IBM T |
| BRS | L2 | 445 | 1 and metalliz\$5 | USPAT; US-PGPUB; EF 3/1/02 15:47 JPO; DERWENT; IBM T |
| BRS | L3 | 23 | 2 and (anti-reflect\$8 (anti adj reflect\$8)) | USPAT; US-PGPUB; EF 3/1/02 15:50 JPO; DERWENT; IBM T |
| BRS | L4 | 89 | 1 and (anti-reflect\$8 (anti adj reflect\$8)) | USPAT; US-PGPUB; EF 3/1/02 15:49 JPO; DERWENT; IBM T |
| BRS | L5 | 182 | 1 and (sion sino sin) | USPAT; US-PGPUB; EP 3/1/02 15:49 JPO; DERWENT; IBM T |
| BRS | L6 | 26 | 5 and (anti-reflect\$8 (anti adj reflect\$8)) | USPAT; US-PGPUB; EP 3/1/02 15:50 JPO; DERWENT; IBM T |
| BRS | <u>L7</u> | 388 | 1 and plasma adj etch\$4 | USPAT; US-PGPUB; EP 3/1/02 15:50 JPO; DERWENT; IBM T |
| BRS | L8 | 23 | 7 and (anti-reflect\$8 (anti adj reflect\$8)) | USPAT; US-PGPUB; EP 3/1/02 15:50 JPO; DERWENT; IBM T |

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| USPAT | Date | Page | Title | Cl/Sub | Cl/Sub | Inventor |
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| | | | | | <u> </u> | · |
| | | | Method for forming a dual inlaid copper | - | 438/618; 438/634; | |
| US 6326301 B1 | 20011204 | 14 | interconnect structure | 438/638 | 438/687; 438/970 | Venkatesan, Suresh, et al. |
| | | | | | 156/345; 430/314; | |
| | | | Fully dry post-via-etch cleaning method | 1 | 430/329 ; 430/330 ; | ł |
| US 6323121 B1 | 20011127 | 9 | for a damascene process | 438/633 | 438/597 ; 438/738 | Liu, Jen-Cheng, et al. |
| | | | Optimized IMD scheme for using | | 438/597; 438/631; | |
| US 6294457 B1 | 20010925 | 7 | organic low-k material as IMD layer | 438/623 | 438/759 ; 438/763 | Liu, Chung-Shi |
| _ | | | | | 430/330 ; 438/710 ; | |
| US 6271115 BI | 20010807 | 11 | Post metal etch photoresist strip method | 438/618 | 438/725 | Liu, Wen Jun, et al. |
| JS 6090697 A | 20000718 | 20 | Etchstop for integrated circuits | 438/618 | 438/643 | Xing, Guoqiang, et al. |
| | | | Elimination of void formation in | | | |
| US 5946589 A | 19990831 | 8 | aluminum based interconnect structures | 438/586 | 438/595 ; 438/688 | Ng, Yat Meng, et al. |
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| | | | ("257/244,245,249,382,503,508,621,622 | | USPAT; US-PGPUB; EPO |
| IS&R | Ll | 3270 | ,632").CCLS. | 3/1/02 14:41 | JPO; DERWENT; IBM TD |
| | | _ | | | USPAT; US-PGPUB; EPO |
| BRS | L2_ | 405 | 1 and contact adj hole | 3/1/02 15:13 | JPO; DERWENT; IBM TD |
| | 1 | ĺ | 4 and ((contact adj hole) opening groove | | USPAT; US-PGPUB; EPO |
| BRS | L5 | 30 | trench) | 3/1/02 15:02 | |
| | ĺ | j | | | USPAT; US-PGPUB; EPC |
| BRS | L6 | 8 | 5 and plasma adj etch\$3 | 3/1/02 15:03 | JPO; DERWENT; IBM TD |
| | | l | | | USPAT; US-PGPUB; EPO |
| IS&R | L12 | 3263 | ("438/396").CCLS. | 3/1/02 15:11 | JPO; DERWENT; IBM TD |
| | ĺ | | | | USPAT; US-PGPUB; EPO |
| BRS | _L13 | 30 | 12 and (arc (antireflective adj coat\$4)) | 3/1/02 15:12 | JPO; DERWENT; IBM TD |
| | | l | | | USPAT; US-PGPUB; EPO |
| BRS | L14 | 9 | 13 and plasma adj etch\$3 | 3/1/02 15:12 | JPO; DERWENT; IBM TD |
| | ; | | 14 and ((contact adj hole) opening | | USPAT; US-PGPUB; EPC |
| BRS | _L15 | 8 | groove trench) | 3/1/02 15:13 | JPO; DERWENT; IBM TD |

Search Result

| USPAT | Date | Page | Title | Cl/Sub | Cl/Sub | Inventor |
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| US | | | Device having metal interconnects with | | | |
| 20010017416 | | | reduced or eliminated metal recess in | Į. | ļ | Sengupta, Samit, Zheng, |
| A1 | | 16 | vias | 1 | | Tammy |
| | | | Silicon oxynitride cap for fluorinated | | | |
| ì | 1 | | silicate glass film in intermetal | ł | 257/632; 257/639; | } |
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| | ŀ | | | | 427/579 ; 438/740 ; | |
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